TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOS VI)

TPCA8128

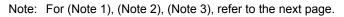
Lithium Ion Battery Applications Power Management Switch Applications

- Small footprint due to compact and slim package
- Low drain-source ON resistance : R_{DS} (ON) = 3.7 m Ω (typ.)
- Low leakage current : $I_{DSS} = -10 \ \mu A \ (max) \ (V_{DS} = -30 \ V)$
- Enhancement mode

: V_{th} = –0.8 to –2.0 V (V_{DS} = –10 V, I_D = –0.5 m A)

Absolute Maximum Ratings (Ta = 25°C)

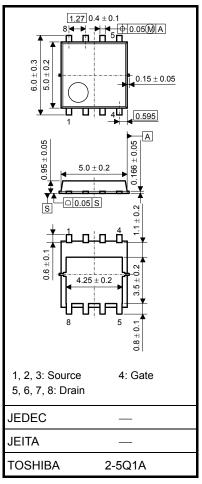
Characteristics			Symbol	Rating	Unit	
Drain-source voltage			V _{DSS}	-30	V	
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)			V _{DGR}	-30	V	
Gate-source voltage			V _{GSS}	-25/+20	V	
Drain current	DC	(Note 1)	۱ _D	-34	А	
	Pulse	(Note 1)	I _{DP}	-102	τ.	
Drain power dissipation (Tc = 25° C)			PD	45	W	
Drain power dissipation (t = 10 s) (Note 2a)			PD	2.8		
Drain power dissipation (t = 10 s) (Note 2b)			PD	1.6		
Single pulse avalanche energy (Note 3)			E _{AS}	150	mJ	
Avalanche cur	Avalanche current			-34	А	
Channel tempe	Channel temperature			150	°C	
Storage temperature range		T _{stg}	–55 to 150	°C		



Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

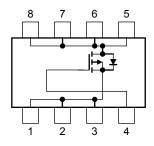
This transistor is an electrostatic-sensitive device. Handle with caution.





Weight: 0.076 g (typ.)

Circuit Configuration

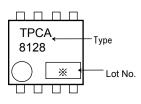


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Thermal Characteristics

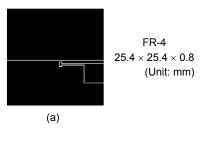
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case (Tc = 25 °C)	R _{th (ch-c)}	2.78	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)	R _{th (ch-a)}	44.6	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2b)	R _{th (ch-a)}	78.1	C/W

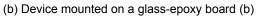
Marking (Note 4)

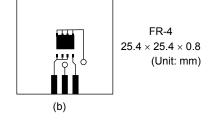


Note 1: The channel temperature should not exceed 150°C during use.

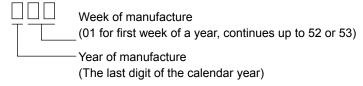
Note 2: (a) Device mounted on a glass-epoxy board (a)







Note 3: $V_{DD} = -24 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), $L = 100 \mu\text{H}$, $R_G = 25 \Omega$, $I_{AR} = -34 \text{ A}$ Note 4: $\overset{\circ}{\times}$ Weekly code: (Three digits)



Electrical Characteristics (Ta = 25°C)

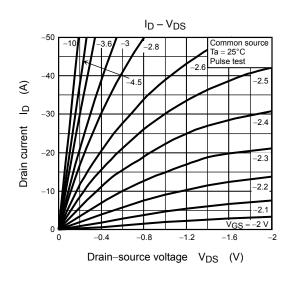
Cha	aracteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	_		±100	nA
Drain cut-off curre	ent	I _{DSS}	V_{DS} = -30 V, V_{GS} = 0 V	_		-10	μA
Drain-source brea	akdown	V (BR) DSS	I _D = –10 mA, V _{GS} = 0 V	-30		_	V
voltage		V (BR) DSX	I _D = -10 mA, V _{GS} = 10 V (Note 5)	-21	10 -30 -21	v	
Gate threshold voltage		V _{th}	V _{DS} = -10 V, I _D = -0.5mA	-0.8		-2.0	V
Drain-source ON resistance			V _{GS} = -4.5 V, I _D = -17 A	_	5.1	6.7	mΩ
Drain-source ON	resistance	R _{DS} (ON)	V _{GS} = -10 V, I _D = -17 A	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	4.8		
Input capacitance		C _{iss}		_	4800	—	pF
Reverse transfer capacitance		C _{rss}	V _{DS} = –10 V, V _{GS} = 0 V, f = 1 MHz		800		
Output capacitance		C _{oss}			900	_	
Switching time	Rise time	tr	$V_{GS} \xrightarrow[-10]{I_D} = -17A$ $I_D = -17A$ $G \xrightarrow[]{G} \xrightarrow[]{G}$	_	11	_	ns
	Turn-on time	t _{on}		_	21		
	Fall time	t _f		_	135	_	
	Turn-off time	t _{off}		_	390	_	
Total gate charge (gate-source plus gate-drain)		Qg	V _{DD} ≈ -24 V, V _{GS} = -10 V		115	_	nC
Gate-source charge 1		Q _{gs1}	I _D = -34 A		11		
Gate-drain ("Miller") charge		Q _{gd}		_	30	_	

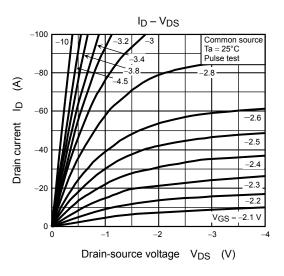
Source-Drain Ratings and Characteristics (Ta = 25°C)

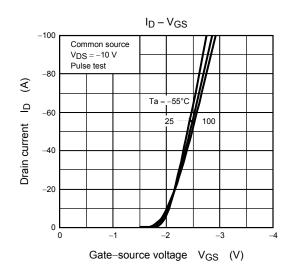
Characterist	ics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse (Note 1)	I _{DRP}	—	_	_	-102	А
Forward voltage (diode)		V _{DSF}	I _{DR} = –34 A, V _{GS} = 0 V			1.2	V

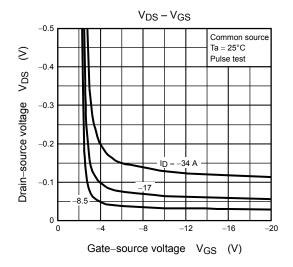
Note 5: V_{DSX} mode (the application of a plus voltage between gate and source) may cause decrease in maximum rating of drain-source voltage.

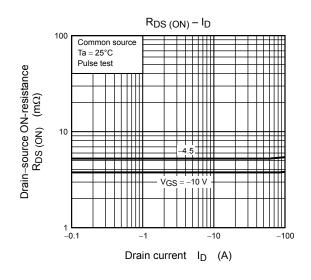
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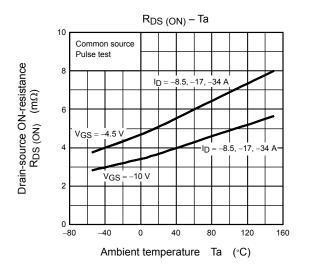


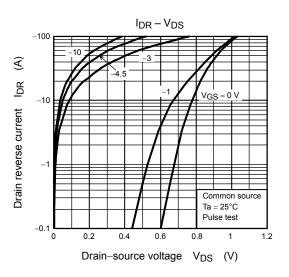


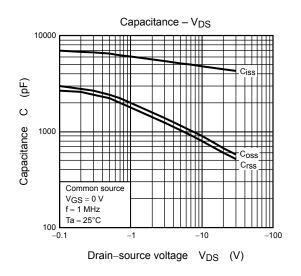


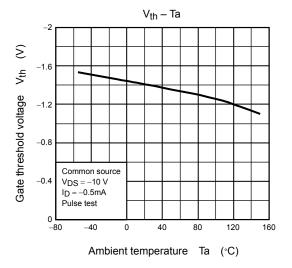


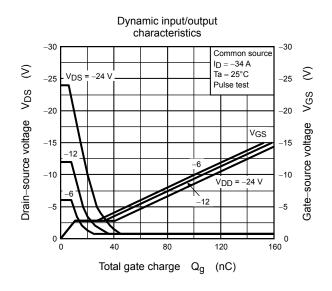
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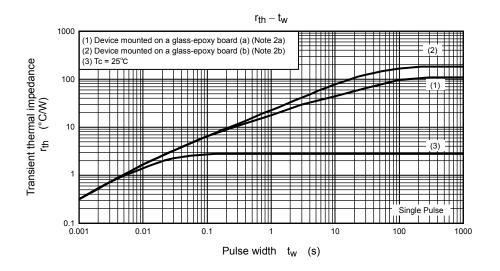


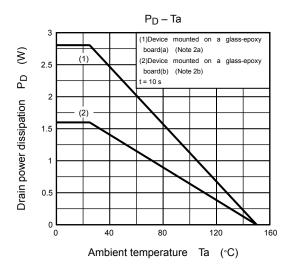


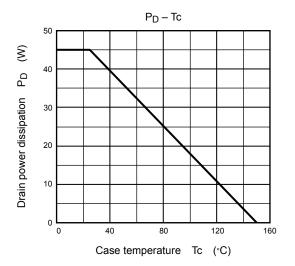


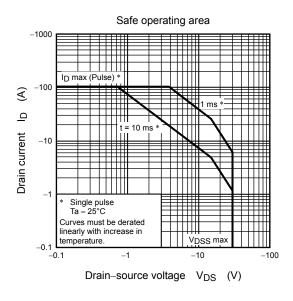












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